

**ABSTRACT**

In an insulated gate semiconductor device (1) having an  $N^-$  type base region (11),  $P^+$  type collector regions (12), P type base regions (13), and  $N^+$  type emitter regions (14), an  $N^+$  type collector-short region (15) which extends toward the  $N^-$  type base region (11) 5 farther than the  $P^+$  type collector regions (12) is formed in the lower surface of the  $N^-$  type base region (11), and a  $P^+$  type semiconductor region (16) is formed between the  $N^+$  type collector-short region (15) and the  $N^-$  type base region (11).